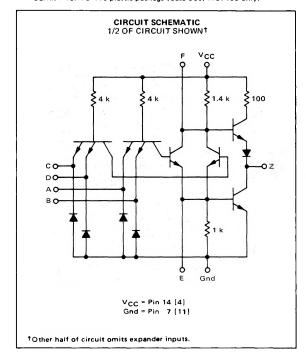
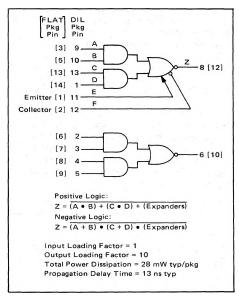
EXPANDABLE DUAL 2-WIDE 2-INPUT "AND-OR-INVERT" GATE

## MC5450 · MC7450

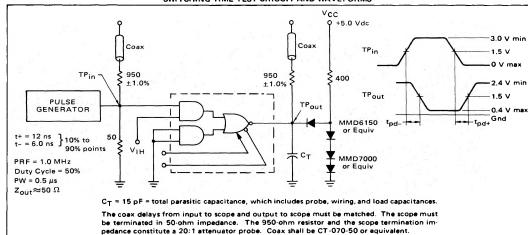
Add Suffix F for TO-86 ceramic package (Case 607).
Suffix L for TO-116 ceramic package (Case 632).
Suffix P for TO-116 plastic package (Case 605) MC7450 only.



This device consists of two AND-OR-INVERT gates, one of which OR expandable. Up to four MC5460/7460 expander gates may be ORed with the device at the expander points.



## SWITCHING TIME TEST CIRCUIT AND WAVEFORMS



## MC5450, MC7450 (continued)

## Emitter [1] 11 \_\_\_\_\_ Collector [2] 12 \_\_\_\_\_ Test procedures are shown for only one gate. The other gates are tested in the same manner. Further, test procedures are shown for only one input of the gate under test. To complete testing, sequence through remaining inputs. ELECTRICAL CHARACTERISTICS

(5) 10 B A (13) 13 C (13) 13 C [14] 1 D

FLAT DIL

9 5 8 6

											3.			TEST (	TEST CURRENT/VOLTAGE VALUES (All Temperatures)	L/VOLTA	GE VA	UES (A	II Tempe	ratures)						-	
								-			Am			-	Ohms				-	Volts	ts						
# <b>&gt;</b>	V= V <sub>CC</sub> = Pin 14 [4] Gnd = Pin 7 [11]	in 7 [	11]						_ŏ	_5	_×	-zx	-K	1×4 R	R <sub>EX</sub> ®	V <sub>EX</sub> ①	>"	> #	> HH	/R	V <sub>R2</sub>	V <sub>th 1</sub>	V <sub>th</sub> 0	۷۵۵	V <sub>CCL</sub> V <sub>C</sub>	V <sub>ССН</sub>	7 111 is
							V	MC5450	16	-0.4	0.41	0.15 -(	-0.15 0	0.3	138	0.4	0.4	2.4		4.5	5.0	2.0		5.0 4	4.50 5.	5.50 gre	grounded for
	2,0						W	MC7450	16	-0.4	0.62	0.27 -(	-0.27 0.	0.43	130	0.4	0.4	2.4	5.5	4.5	5.0	2.0	8.0	5.0 4	4.75 5.	5. 25 all	all tests in
	- yk -4.	£ ]	-	MC5450 Test Limits -55 to +195°C	Limits	MC74	MC7450 Test Limits	Limits					TE.	ST CUR	FEST CURRENT/VOLTAGE APPLIED TO PINS LISTED BELOW:	<b>JLTAGE</b>	APPLIE	D TO P	NS LIST	ED BELO	. W.		1 31			the be	the pins listed below:
Characteristic	Symbol	Test	2	Max	Unit	Min	Max	, iii	_6	_6	-i×	-zx	_x	l <sub>x4</sub>	R <sub>EX</sub> ®	VEX®	>"	>=	V <sub>IHH</sub>	VRI	V <sub>R2</sub>	۷#۲	V <sub>th</sub> 0	V <sub>CC</sub>	VCCL	VCCH	Gnd
Input Forward Current	j.	Ω		-1.6	mAdc		-1.6	mAdc					30				Ω			O				I	-	>	*
Leakage Current	<sup>L</sup> R1	Ω		40	μAdc		40	μAdc									1	Q				1,	1	,		>	A,B,C*
	I <sub>R2</sub>	Q	1	1.0	mAdc		1.0	mAdc	1.		177	1,0						i.	Ω			1	1	1,	,	Δ	A,B,C*
Expander Input Current	<sup>1</sup> EX	F ①	1.	-2.9#	mAdc		-3.1#	mAdc	N					1		ਜ,ਸ		1		10		1		,	>	1.	A,B,C*,D
Base-Emitter Voltage	VBE	E (2)		1.0#	Vdc	T.	1.0#	Vdc	Z		E, F	1	1.	-			3.5		.1.		1,			,	>		A,B,C*,D
Output Output Voltage	N <sub>OL</sub>	N	1	0.4	Vdc	100	4.0	Vdc	N		100		1	1 2 2 2	1							C,D	-		>	<del> </del>	A,B*
		© Z		0.4	Vdc	12	0.4	Vdc	z	1.	1.			ы	ſ4				1			C,D	1		>		A,B
	МОМ	z	2.4		Vdc	2.4		Vdc		2	11		Ž.,			1		1		U		1.	Q	1	>		A,B*
	1.1	N	2.4#		Vdc	2.4#		Vdc	1	N		ш	Ĺt.	1		1	1 50		- 1	1		t	i,	,	>		A,B,C*,D
Short-Circuit Current	$^{1}\mathrm{sc}^{\dagger}$	Z	-20	-55	mAdc	-18	-55	mAdc	1		1	,	1							4	· 4 ·				-	>	A,B,C*, D,Z
Power Requirements (Total Device) Power Supply Drain	HQdI	Δ		14	mAdc		14	mAdc		11		1	1		1	r	i		1.1		All				<u> </u>	>	ı
	IPDL	Λ	1	8.0	mAdc		8.0	mAdc	1		1				. 1		1	,	1			,	. /			>	A,B,C*,D
Switching Parameters									Pulse	Pulse Out			1037							1 m							
Turn-On Delay	t pd-	D,Z		15**	ns	1	15**	ns	D	Z		Territ		110			1	υ	1	1		1	-1	>		,	A,B*
Turn-Off Delay	t pd+	D,Z		29**	su		29**	su	Q	Z								υ	1			1		>		<b>-</b>	A,B*
				1	1	1	1	1	1	-	1	1	1	1	1	1	1	1	1	1		1	1	1	1	1	

#Tested only at low temperature limit. \*Ground inputs to gate not under test.  $\,$  †Only one output should be shorted at a time. \*\* Trested only at 25°C.

① See Figure 1.
② See Figure 2.
③ See Figure 3.

FIGURE 1 - IEX TEST CIRCUIT

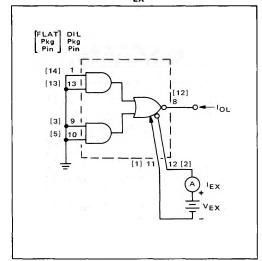


FIGURE 2 - VBE TEST CIRCUIT

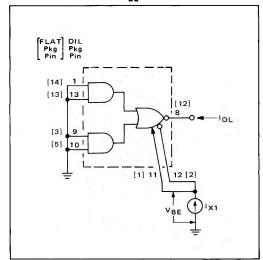


FIGURE 3 - VOL TEST CIRCUIT

